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Low Supply-Voltage
 Operation . . . V<sub>CC</sub> = ±1 V Min

 Wide Bandwidth . . . 7 MHz Typ at V<sub>CC</sub>± = ±2.5 V

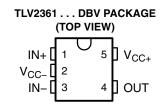
High Slew Rate . . . 3 V/μs Typ at V<sub>CC</sub>± = ±2.5 V

• Wide Output Voltage Swing . . .  $\pm 2.4$  V Typ at V<sub>CC</sub> $\pm = \pm 2.5$  V, R<sub>L</sub> = 10 k $\Omega$ 

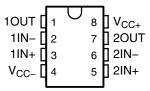
• Low Noise . . . 8 nV/ $\sqrt{\text{Hz}}$  Typ at f = 1 kHz

#### description/ordering information

The TLV236x devices are high-performance dual operational amplifiers built using an original Texas Instruments bipolar process. These devices can be operated at a very low supply



TLV2362 . . . D, DGK, P, PS, OR PW PACKAGE (TOP VIEW)



voltage ( $\pm 1$  V), while maintaining a wide output swing. The TLV236x devices offer a dramatically improved dynamic range of signal conditioning in low-voltage systems. The TLV236x devices also provide higher performance than other general-purpose operational amplifiers by combining higher unity-gain bandwidth and faster slew rate. With their low distortion and low-noise performance, these devices are well suited for audio applications.

#### **ORDERING INFORMATION**

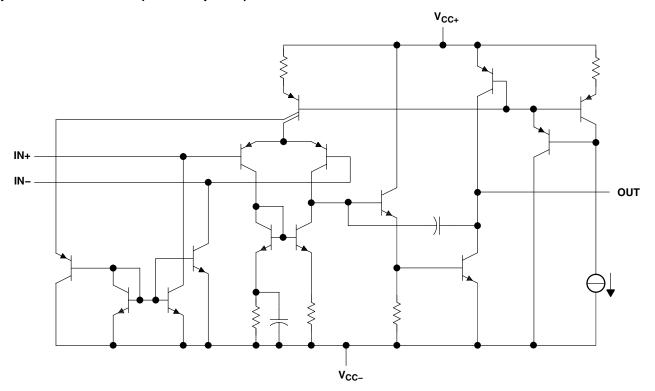
T <sub>A</sub>	PACKAGE	:t	ORDERABLE PART NUMBER	TOP-SIDE MARKING <sup>‡</sup>		
200 1 - 7000	00T 00 5 (DD)/\	Reel of 3000	TLV2361CDBVR	VOO		
–0°C to 70°C	SOT-23-5 (DBV)	Reel of 250	TLV2361CDBVT	MARKING <sup>‡</sup> YC3_ YC4_ YBS TLV2362IP 2362I TY2362		
	00T 00 5 (DD)/\	Reel of 3000	TLV2361IDBVR	V04		
	SOT-23-5 (DBV)	Reel of 250	TLV2361IDBVT	_		
	MSOP/VSSOP (DGK)	Reel of 2500	TLV2362IDGKR	YBS		
	PDIP (P)	Tube of 50	TLV2362IP	TLV2362IP		
-40°C to 85°C	COIC (D)	Tube of 75	TLV2362ID	00001		
	SOIC (D)	Reel of 2500	TLV2362IDR	23021		
	SOP (PS)	Reel of 2000	TLV2362IPSR	TY2362		
	TCCOD (DW)	Tube of 150	TLV2362IPW	YBS TLV2362IP 2362I		
	TSSOP (PW)	Reel of 2000	TLV2362IPWR	112302		

<sup>&</sup>lt;sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

<sup>&</sup>lt;sup>‡</sup> DBV: The actual top-side marking has one additional character that designates the wafer fab/assembly site.

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# equivalent schematic (each amplifier)



ACTUAL DEVICE	COMPONE	NT COUNT
COMPONENT	TLV2361	TLV2362
Transistors	30	46
Resistors	6	11
Diodes	1	1
Capacitors	2	4
JFET	1	1

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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V <sub>CC+</sub> (see Note 1)		3.5 V
Supply voltage, V <sub>CC</sub> (see Note 1)		
Differential input voltage, V <sub>ID</sub> (see Note 2)		
Input voltage, V <sub>I</sub> (any input) (see Notes 1 and 3)		
Output voltage, V <sub>O</sub>		
Output current, I <sub>O</sub>		
Duration of short-circuit current at (or below) 25°C		
Package thermal impedance, θ <sub>.IA</sub> (see Notes 4 an	` .	
J / WA (	DBV package	
	DGK package	
	P package	
	PS package	
	PW package	
Operating virtual junction temperature, T.J		
Lead temperature 1,6 mm (1/16 inch) from case for		
Storage temperature range, T <sub>stq</sub>		
- · · · · · · · · · · · · · · · · · · ·		

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between  $V_{CC-}$  and  $V_{CC-}$ 

- 2. Differential voltages are at IN+ with respect to IN-.
- All input voltage values must not exceed V<sub>CC</sub>.
   Maximum power dissipation is a function of T<sub>J</sub>(max), θ<sub>JA</sub>, and T<sub>A</sub>. The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_J(max) - T_A)/\theta_{JA}$ . Selecting the maximum of 150°C can affect reliability.
- 5. The package thermal impedance is calculated in accordance with JESD 51-7.

#### recommended operating conditions

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	±1	±2.5	V
_	TLV2361C	0	70	°C
IA	Operating free-air temperature TLV2361I, TLV2362I	-40	85	-0

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# TLV2361 and TLV2362 electrical characteristics, $V_{CC}\pm$ = $\pm1.5$ V (unless otherwise noted)

	PARAMETER	TI	EST CONDITIONS		T <sub>A</sub>	MIN	TYP	MAX	UNIT	
V	Innut offeet veltage	V 0			25°C		1	6	mV	
V <sub>IO</sub>	Input offset voltage	$V_{O} = 0$ ,	$V_{IC} = 0$		Full range			7.5	mv	
	Innut offeet ourrent	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	V 0		25°C		5	100	nA	
I <sub>IO</sub>	Input offset current	$V_{O}=0,$	$V_{IC} = 0$		Full range			150	ΠA	
	Innut high gurrant	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	V 0		25°C		20	150	nA	
I <sub>IB</sub>	Input bias current	$V_{O}=0,$	$V_{IC} = 0$	Full range			250	ΠA		
\	Common-mode input	V <sub>IO</sub>   ≤ 7.5 mV		25°C	±0.5			v		
V <sub>IC</sub>	voltage	V  O  ≥ 7.5 IIIV			Full range	±0.5			V	
Maximum positive-peak		$R_L = 10 \text{ k}\Omega$		25°C	1.2	1.4		V		
V <sub>OM</sub> +	output voltage	$R_L \ge 10 \ k\Omega$		Full range	1.2			V		
.,	Maximum negative-peak	$R_L = 10 \text{ k}\Omega$			25°C	-1.2	-1.4		٧	
V <sub>OM</sub> -	output voltage	$R_L \ge 10 \ k\Omega$			Full range	-1.2			V	
	Supply current	., .	Nalaad		25°C		1.4	2.25	mA	
Icc	(per amplifier)	$V_O = 0$ ,	No load		Full range			2.75	mA	
	Large-signal differential	V 14 V	D 1010	TLV2361	25°C	60	80		dB	
A <sub>VD</sub>	voltage amplification	$V_O = \pm 1 \text{ V},$ $R_L = 10 \text{ k}\Omega$		TLV2362	25 0		55		aB	
CMRR	Common-mode rejection ratio	$V_{IC} = \pm 0.5 \text{ V}$	25°C		75		dB			
k <sub>SVR</sub>	Supply-voltage rejection ratio	$V_{CC} \pm = \pm 1.5 \text{ V t}$	to ±2.5 V		25°C		80		dB	

# TLV2361 and TLV2362 operating characteristics, $V_{CC}\pm=\pm1.5$ V, $T_A=25^{\circ}C$

	PARAMETER		TEST CONDITIONS					
SR	Slew rate	$A_V = 1$ ,	$V_{I} = \pm 0.5 \text{ V}$		2.5	V/μs		
B <sub>1</sub>	Unity-gain bandwidth	$A_V = 40,$	$R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 100 pF	6	MHz		
V <sub>n</sub>	Equivalent input noise voltage	$R_S = 100 \Omega$ ,	$R_F = 10 \text{ k}\Omega$ ,	f = 1 kHz	9	nV/√ <del>Hz</del>		

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# TLV2361 and TLV2362 electrical characteristics, $V_{CC}\pm$ = $\pm2.5$ V (unless otherwise noted)

	PARAMETER	Т	EST CONDITIONS	3	T <sub>A</sub>	MIN	TYP	MAX	UNIT	
V	Innut offeet veltage	V 0			25°C		1	6	m)/	
$V_{IO}$	Input offset voltage	$V_{O} = 0$ ,	$V_{IC} = 0$	Full range			7.5	mV		
1	Input offset current	V 0	$V_{O} = 0,$ $V_{IC} = 0$		25°C		5	100	4	
I <sub>IO</sub>	Input offset current	$V_O = 0$ ,	Full range			150	nA			
	Innut high augment	V 0	V 0		25°C		20	150	~ ^	
I <sub>IB</sub>	Input bias current	$V_{O} = 0$ ,	$V_{IC} = 0$	Full range			250	nA		
V	Common-mode input		V <sub>IO</sub>   ≤ 7.5 mV		25°C	±1.5			٧	
$V_{IC}$	voltage	V <sub>10</sub>   ≥ 7.5 mV		Full range	±1.4			V		
W	Maximum positive-peak	$R_L = 10 \text{ k}\Omega$	25°C	2	2.4		V			
$V_{OM+}$	output voltage	$R_L \geq 10 \; k\Omega$		Full range	2			V		
.,	Maximum negative-peak	$R_L = 10 \text{ k}\Omega$			25°C	-2	-2.4		V	
$V_{OM-}$	output voltage	$R_L \ge 10 \ k\Omega$		Full range	-2			V		
,	Supply current		No local		25°C		1.75	2.5	4	
Icc	(per amplifier)	$V_{O} = 0$ ,	No load		Full range			3	mA	
	Large-signal differential	V 14.V	D 4010	TLV2361	0500	60	80		40	
$A_{VD}$	voltage amplification	$V_O = \pm 1 V$ ,	$=\pm 1 \text{ V}, \qquad \qquad R_L = 10 \text{ k}\Omega$		25°C		60		dB	
CMRR	Common-mode rejection ratio	$V_{IC} = \pm 0.5 \text{ V}$		25°C		85		dB		
k <sub>SVR</sub>	Supply-voltage rejection ratio	$V_{CC}^{\pm} = \pm 1.5 \text{ V}$	to ±2.5 V		25°C		80	_	dB	

# TLV2361 and TLV2362 operating characteristics, $V_{CC}\pm$ = $\pm 2.5$ V, $T_{A}$ = $25^{\circ}C$

	PARAMETER		TEST CONDITIONS					
SR	Slew rate	$A_V = 1$ ,	$V_{I} = \pm 0.5 \text{ V}$		3	V/µs		
B <sub>1</sub>	Unity-gain bandwidth	$A_V = 40,$	$R_L = 10 \text{ k}\Omega$ ,	C <sub>L</sub> = 100 pF	7	MHz		
V <sub>n</sub>	Equivalent input noise voltage	$R_S = 100 \Omega$ ,	$R_F = 10 \text{ k}\Omega$ ,	f = 1 kHz	8	nV/√ <del>Hz</del>		
THD + N	Total harmonic distortion, plus noise	$A_V = 1$ ,	$V_0 = \pm 1.2 \text{ V},$	$R_L = 10 \text{ k}\Omega$ , $f = 3 \text{ kHz}$	0.004	%		

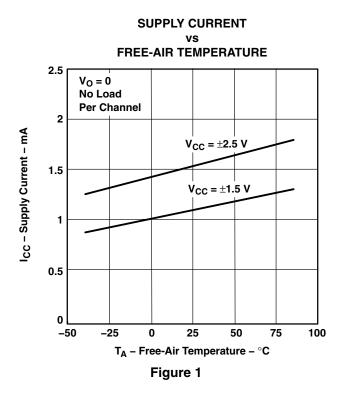
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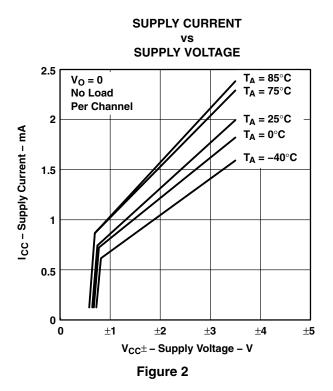
## **TYPICAL CHARACTERISTICS**

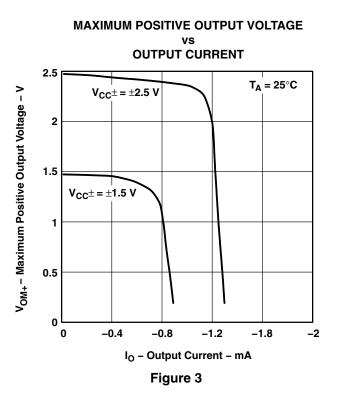
## **Table of Graphs**

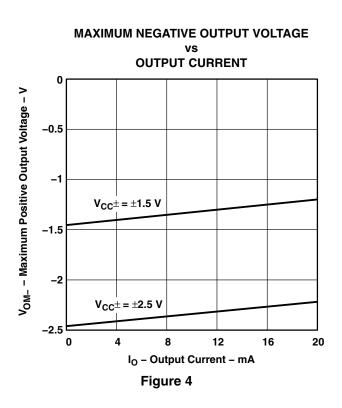
•	
GRAPH TITLE	FIGURE
Supply current vs Free-air temperature	1
Supply current vs Supply voltage	2
Maximum positive output voltage vs Output current	3
Maximum negative output voltage vs Output current	4
Maximum peak-to-peak output voltage vs Frequency	5
Equivalent input noise voltage vs Frequency	6
Total harmonic distortion vs Frequency	7
Total harmonic distortion vs Output voltage	8

#### TYPICAL CHARACTERISTICS



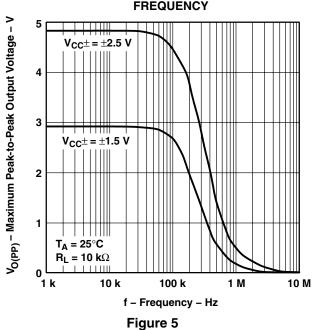




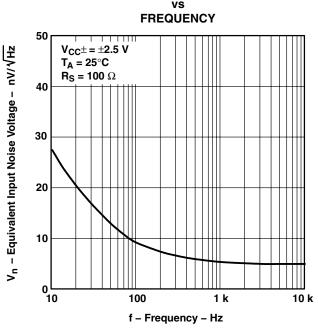


#### TYPICAL CHARACTERISTICS

# MAXIMUM PEAK-TO-PEAK OUTPUT VOLTAGE vs FREQUENCY

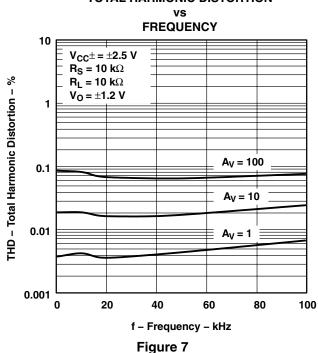


# EQUIVALENT INPUT NOISE VOLTAGE



## Figure 6

### TOTAL HARMONIC DISTORTION



#### **TOTAL HARMONIC DISTORTION**

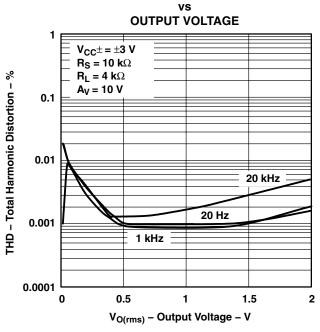


Figure 8

#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2361CDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	0 to 70	(YC3B, YC3G, YC3J, YC3L)	Samples
TLV2361CDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	0 to 70	(YC3B, YC3G, YC3J, YC3L)	Samples
TLV2361IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(YC4B, YC4G, YC4J, YC4L)	Samples
TLV2361IDBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 85	(YC4B, YC4G, YC4J, YC4L)	Samples
TLV2362ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	23621	Samples
TLV2362IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(YBL, YBS, YBU)	Samples
TLV2362IDGKRG4	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	(YBL, YBS, YBU)	Samples
TLV2362IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	23621	Samples
TLV2362IP	ACTIVE	PDIP	Р	8	50	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	TLV2362IP	Samples
TLV2362IPWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY2362	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

#### PACKAGE OPTION ADDENDUM

13-Aug-2021

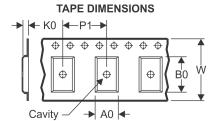
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TAPE AND REEL INFORMATION





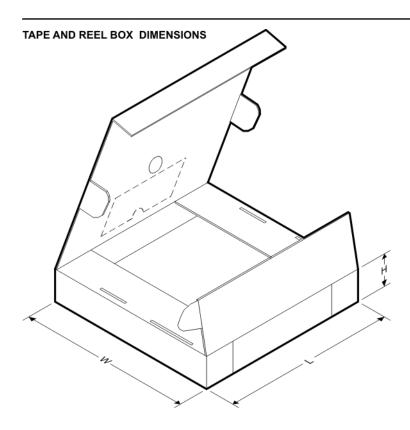
	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2361CDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV2361CDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2361CDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2361CDBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV2361IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2361IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV2361IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV2361IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV2362IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.3	1.3	8.0	12.0	Q1
TLV2362IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV2362IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1

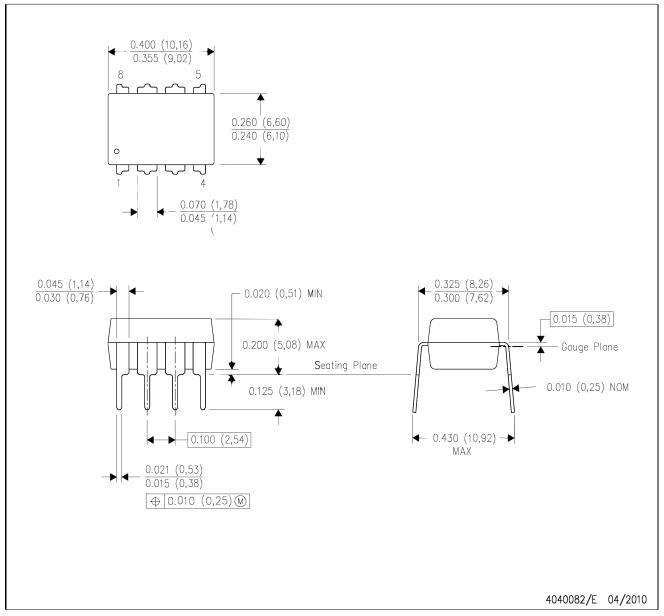


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2361CDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2361CDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2361CDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2361CDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2361IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2361IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV2361IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2361IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
TLV2362IDGKR	VSSOP	DGK	8	2500	346.0	346.0	35.0
TLV2362IDR	SOIC	D	8	2500	340.5	336.1	25.0
TLV2362IPWR	TSSOP	PW	8	2000	853.0	449.0	35.0

# P (R-PDIP-T8)

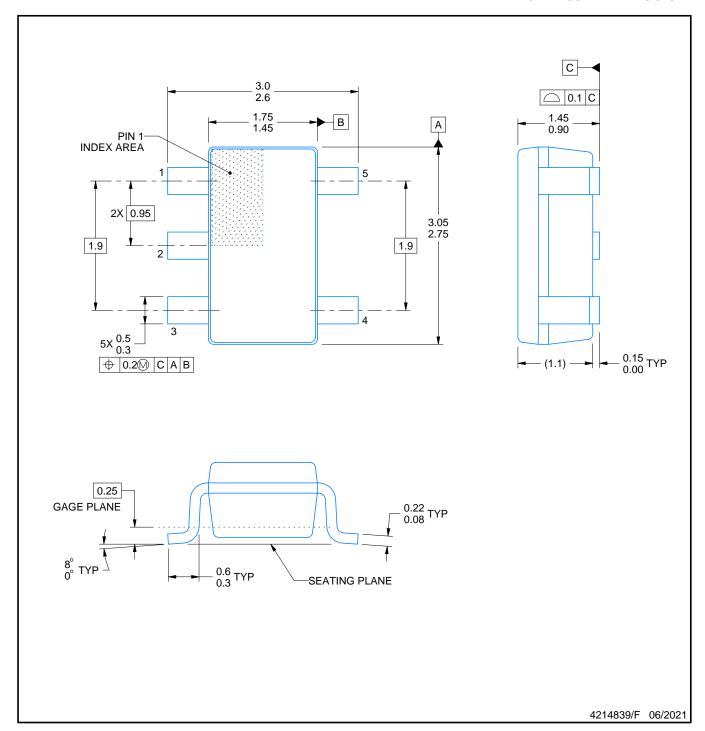
# PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



SMALL OUTLINE TRANSISTOR



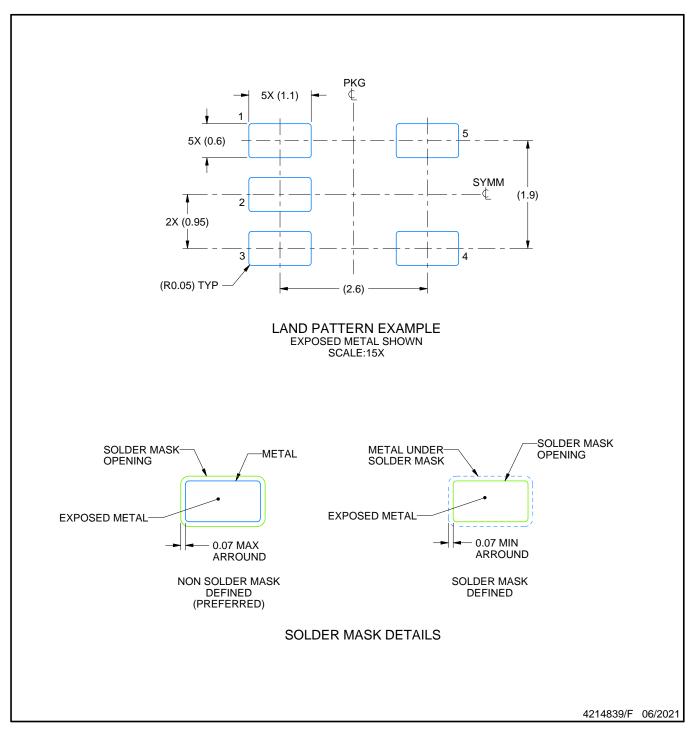
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

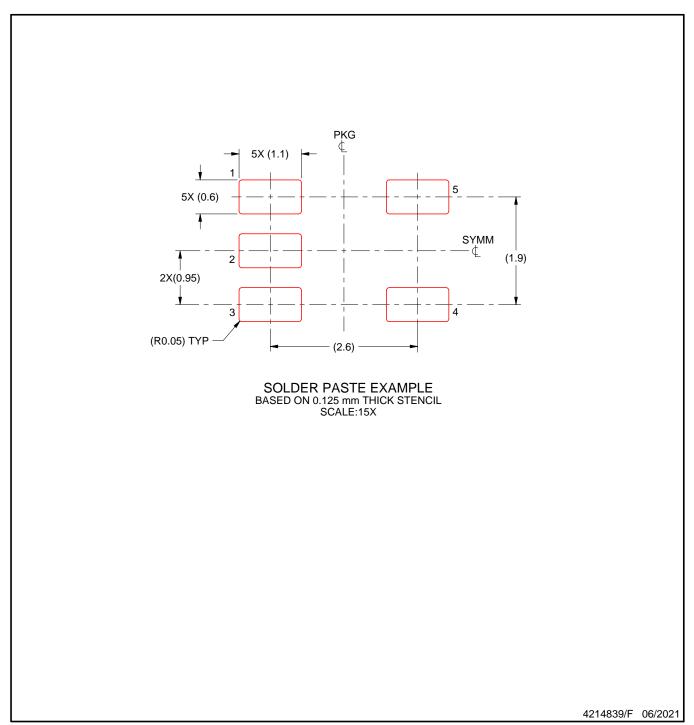
SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



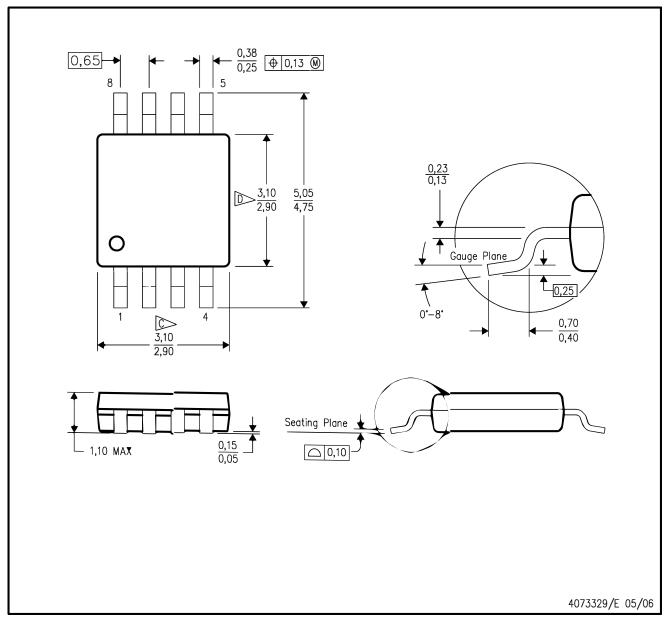
NOTES: (continued)

<sup>7.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

<sup>8.</sup> Board assembly site may have different recommendations for stencil design.

# DGK (S-PDSO-G8)

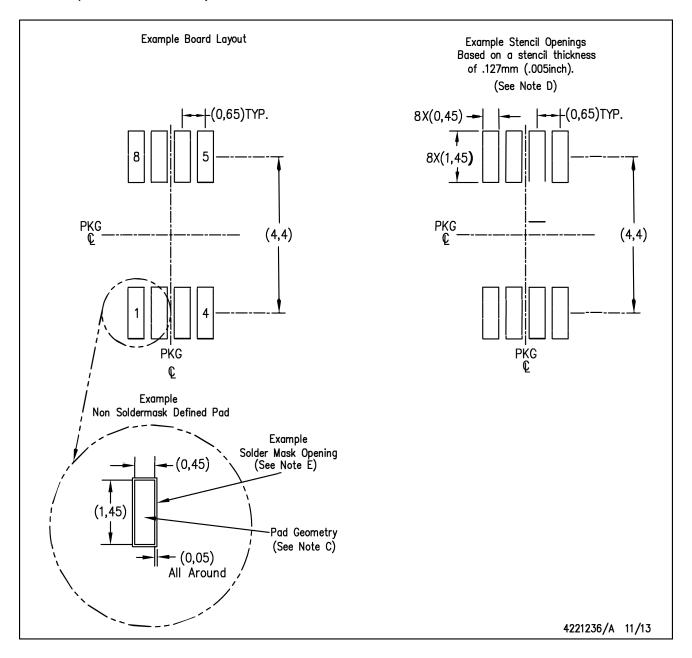
# PLASTIC SMALL-OUTLINE PACKAGE



- : A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
  - Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
  - E. Falls within JEDEC MO-187 variation AA, except interlead flash.

# DGK (S-PDSO-G8)

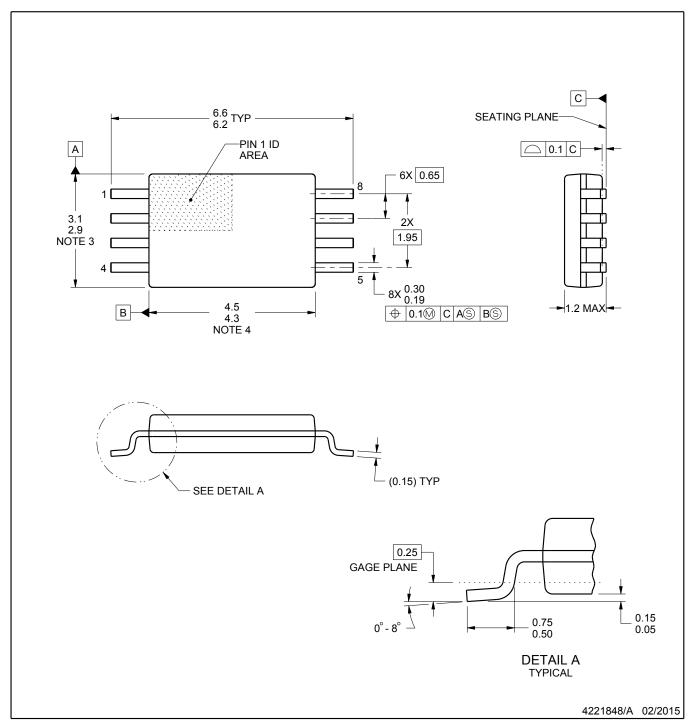
# PLASTIC SMALL OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



SMALL OUTLINE PACKAGE

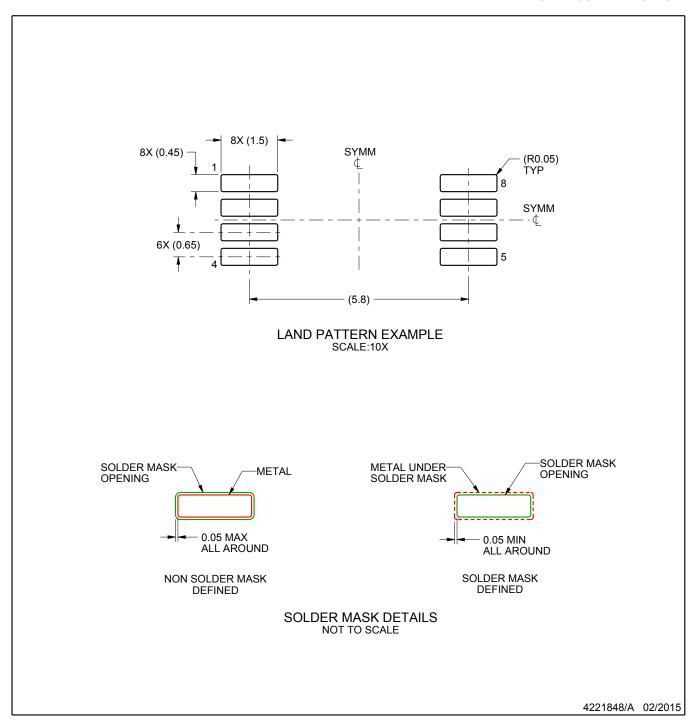


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.

SMALL OUTLINE PACKAGE

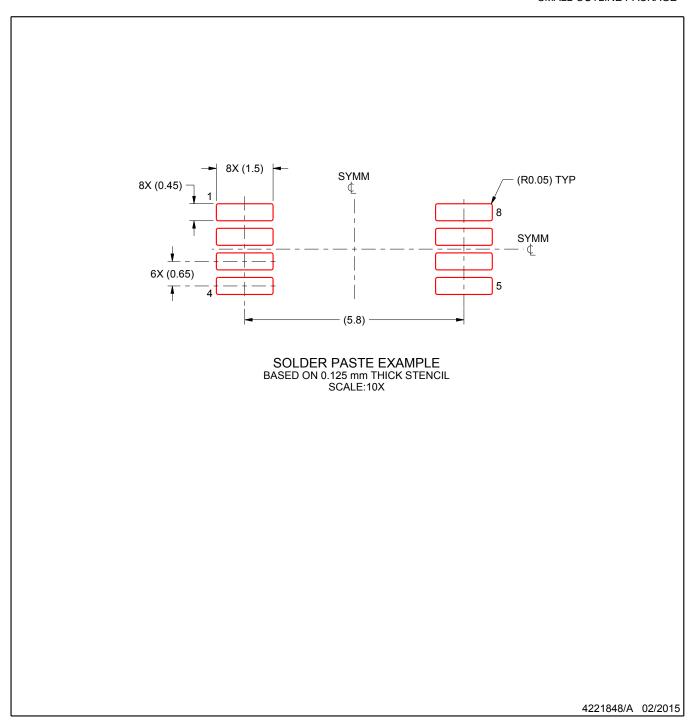


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE PACKAGE

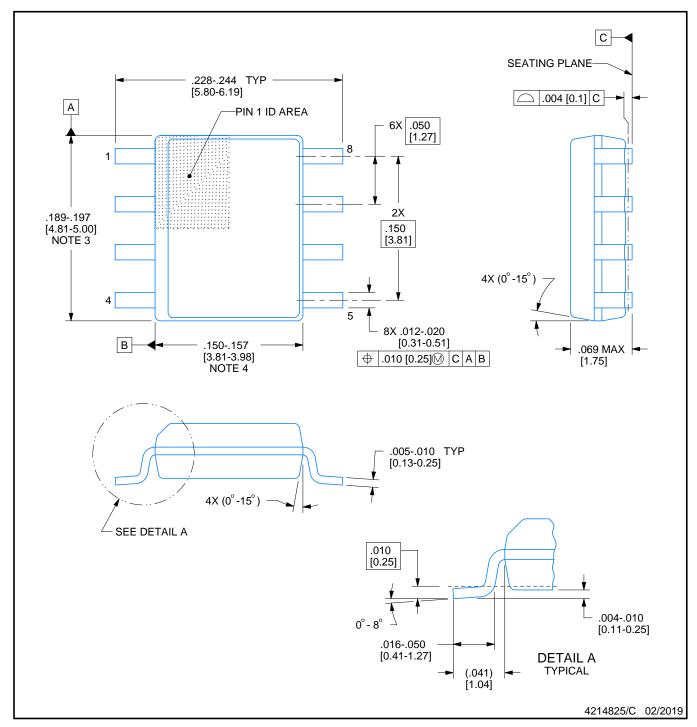


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

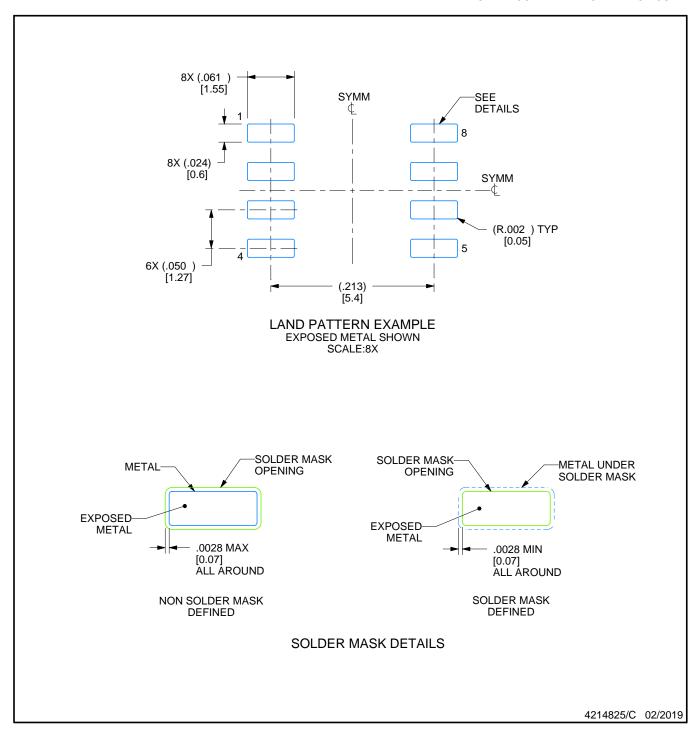


SMALL OUTLINE INTEGRATED CIRCUIT



- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.

SMALL OUTLINE INTEGRATED CIRCUIT

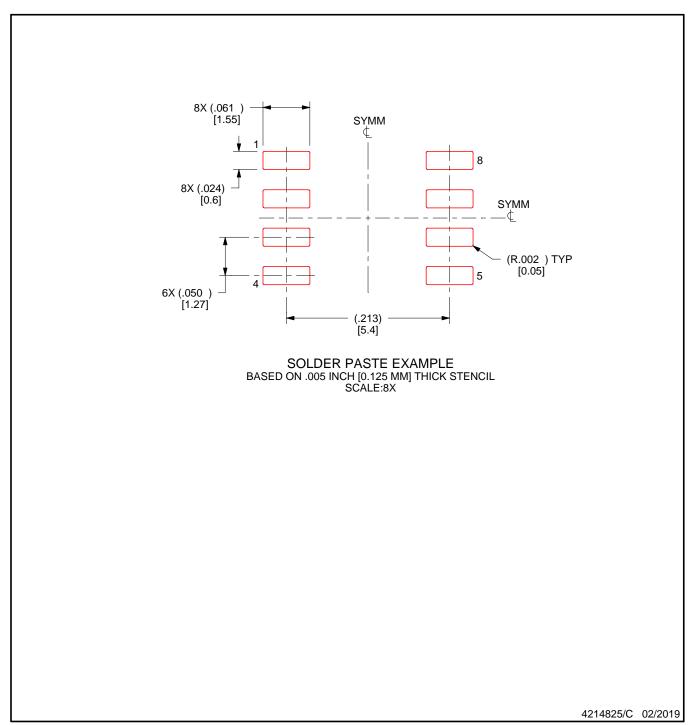


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.